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28/1978  
437862

1 TRENCH DMOS POWER TRANSISTOR WITH  
2 FIELD-SHAPING BODY PROFILE AND  
3 THREE-DIMENSIONAL GEOMETRY  
4

5 Constantin Bulucea  
6 Rebecca Rossen  
7

8 ABSTRACT

9 Power MOSFET apparatus, and method for its production,  
10 that suppresses voltage breakdown near the gate, using a  
11 polygon-shaped trench in which the gate is positioned, using  
12 a shaped deep body junction that partly lies below the  
13 trench bottom, and using special procedures for growth of  
14 gate oxide at various trench corners.

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